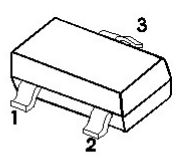


TRANSISTOR(NPN)	SOT-23 Plastic-Encapsulate Transistors
<p>SOT-23</p>  <p>1. BASE 2. EMITTER 3. COLLECTOR</p> <p>Marking: 1AM</p>	<p>Features</p> <ul style="list-style-type: none"> ● Complementary to MMBT3906 ● Power Dissipation of 200mW ● High Stability and High Reliability <p>Mechanical Data</p> <ul style="list-style-type: none"> ● SOT-23 Small Outline Plastic Package ● Epoxy UL: 94V-0 ● Mounting Position: Any

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter -Base Voltage	V _{EBO}	6	V
Collector Current-Continuous	I _c	200	mA
Collector Power Dissipation	P _c	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}	625	°C/W

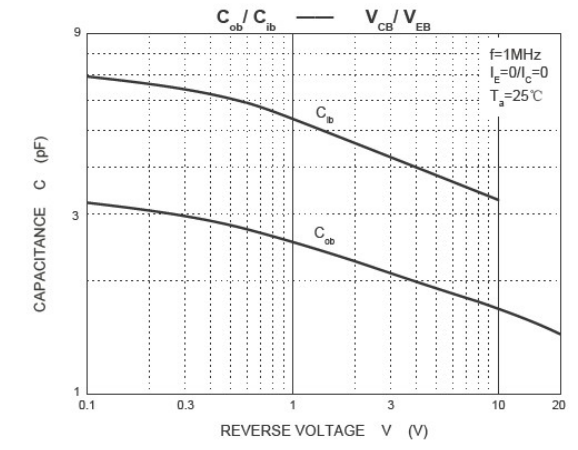
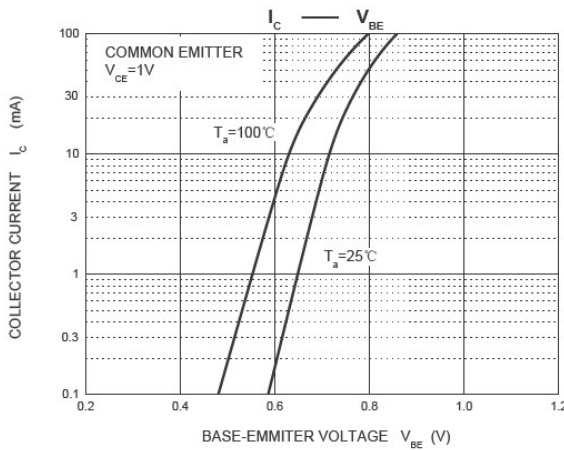
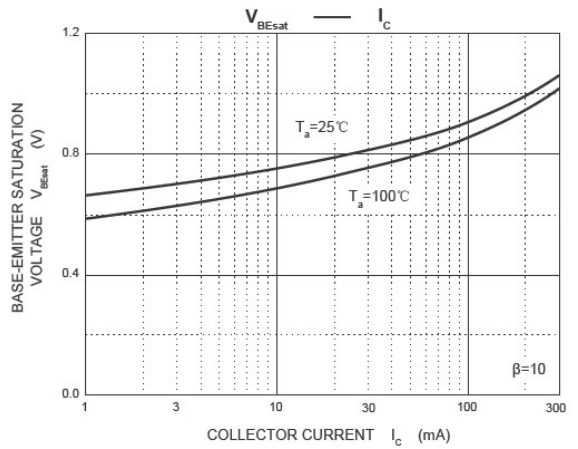
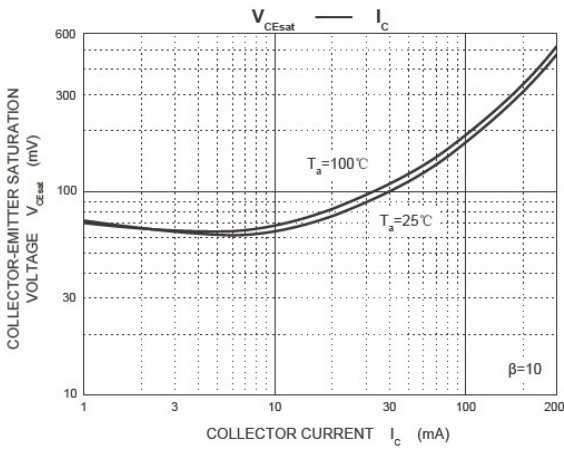
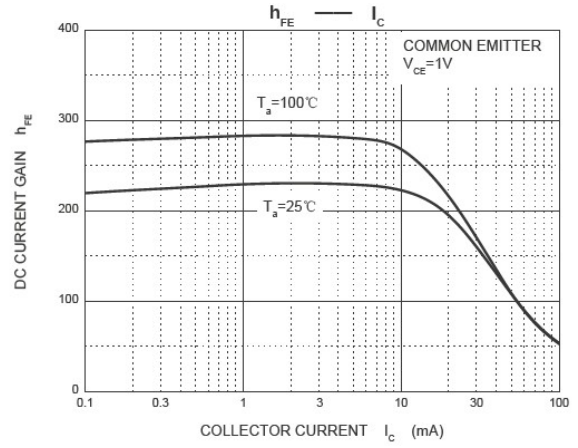
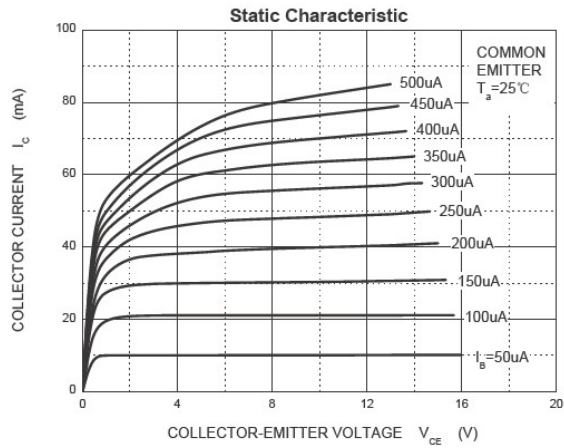
Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

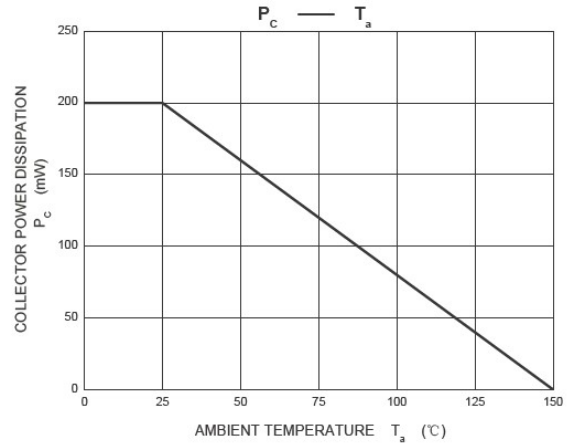
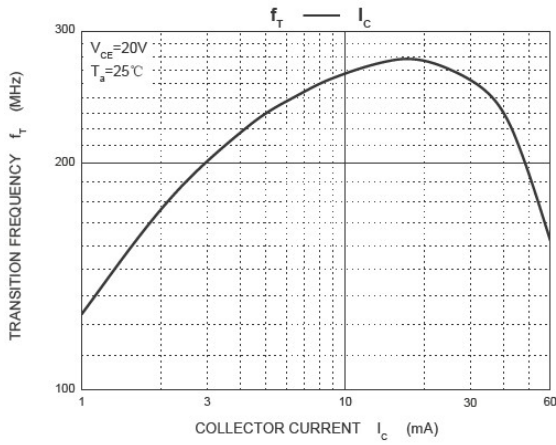
Parameter	Symbols	Test Condition	Limits		Unit
			Min	Max	
Collector-base breakdown voltage	V(BR)CBO	I _C =10uA, I _E =0	60		V
Collector-emitter breakdown voltage	V(BR)CEO	I _C =1mA, I _B =0	40		V
Emitter-base breakdown voltage	V(BR)EBO	I _E =10uA, I _C =0	6		V
Collector cut-off current	I _{CEX}	V _{CE} =30V, V _{EB(off)} =3V		50	nA
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0		100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0		100	nA
DC current gain	hFE(1)	V _{CE} =1V, I _C =10mA	100	300	
	hFE(2)	V _{CE} =1V, I _C =50mA	60		
	hFE(3)	V _{CE} =1V, I _C =100mA	30		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50mA, I _B =5mA		0.30	V
Base -emitter saturation voltage	V _{BE(sat)}	I _C =50mA, I _B =5mA		0.95	V
Transition frequency	f _T	V _{CE} =20V, I _C =10mA, f=100MHz	300		MHz
Delay time	t _d	V _{CC} =3V, V _{BE(off)} =-0.5V, I _C =10mA, I _{B1} =1mA		35	nS
Rise time	t _r	V _{CC} =3V, V _{BE(off)} =-0.5V, I _C =10mA, I _{B1} =1mA		35	nS
Storage time	t _s	V _{CC} =3V, I _C =10mA, I _{B1} =I _{B2} =1mA		200	nS
Fall time	t _f	V _{CC} =3V, I _C =10mA, I _{B1} =I _{B2} =1mA		50	nS

CLASSIFICATION OF hFE(1)

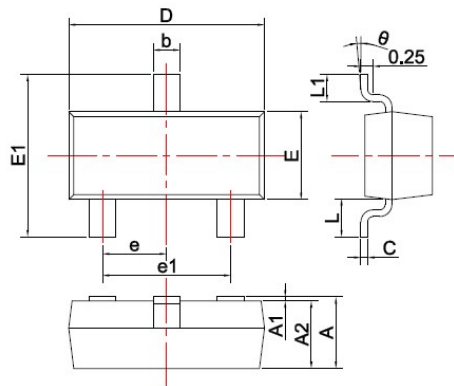
HFE	100-300	
RANK	L	H
RANGE	100-200	200-300

Typical characteristics





SOT-23 PACKAGE OUTLINE Plastic surface mounted package

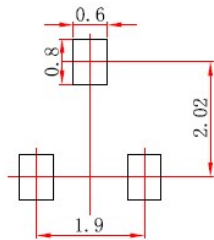


SYMBOL	DIMENSIONS	
	MIN	MAX
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
theta	0°	8°

Unit: mm

Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



- Note:
1. Controlling dimension: In millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)